US005942749A

United States Patent [19]

Takeuchi et al.

[11] Patent Number: 5,942,749

[45] Date of Patent: Aug. 24, 1999

[54] **PHOTODETECTOR HAVING MEANS FOR PROCESSING OPTICAL INPUT SIGNALS**

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[21] Appl. No.: **08/901,629**

[22] Filed: **Jul. 28, 1997**

[30] **Foreign Application Priority Data**

Jul. 29, 1996 [JP] Japan 8-198964

[51] **Int. Cl.**[6] **H01J 40/14**

[52] **U.S. Cl.** ..... **250/214.1**; 250/214 LA; 257/435; 257/461

[58] **Field of Search** ..... 250/214.1, 214 R, 250/214 LA, 214 LS; 257/435, 461, 432

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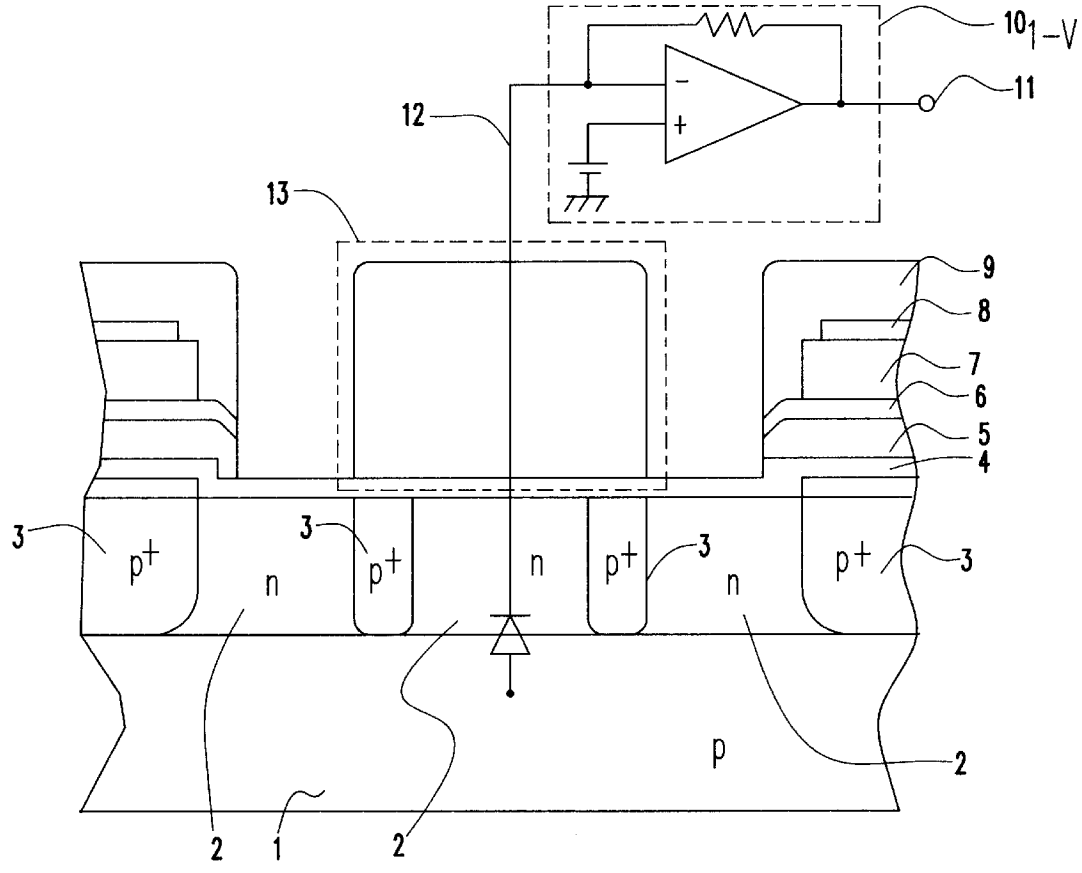
Primary Examiner—Que T. Le

Attorney, Agent, or Firm—Whitham, Curtis & Whitham

[57] **ABSTRACT**

A photodetector with a signal processing capability processes optical input signals therein. The photodetector has a first input area and a second input area which are optically isolated from each other, but electrically connected to each other due to crosstalk characteristics to operate as a two-input adder.

17 Claims, 7 Drawing Sheets



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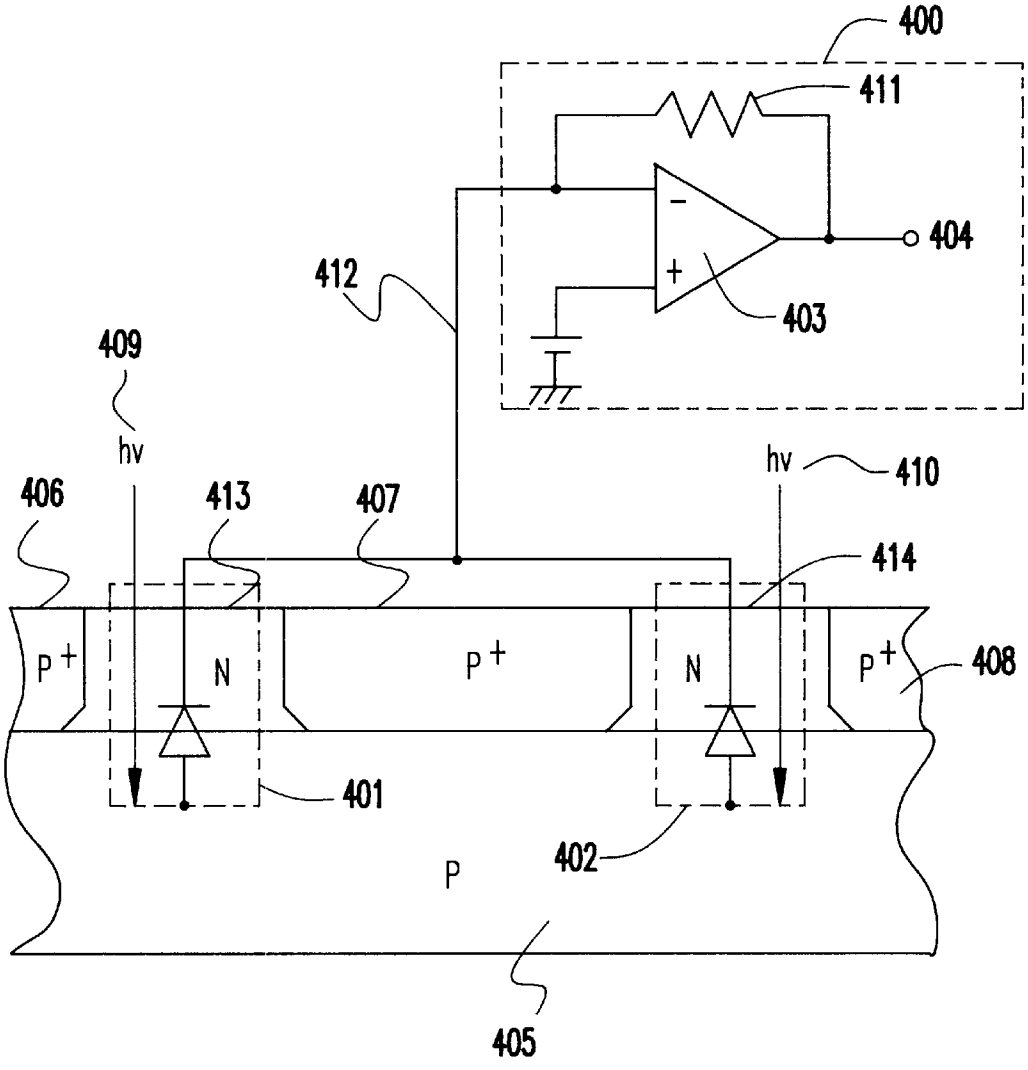

FIG. 1 PRIOR ART

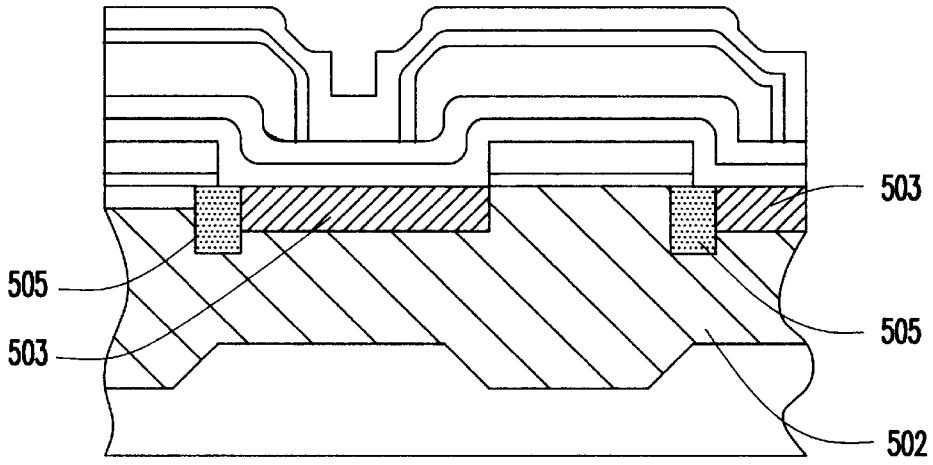

FIG.2 PRIOR ART

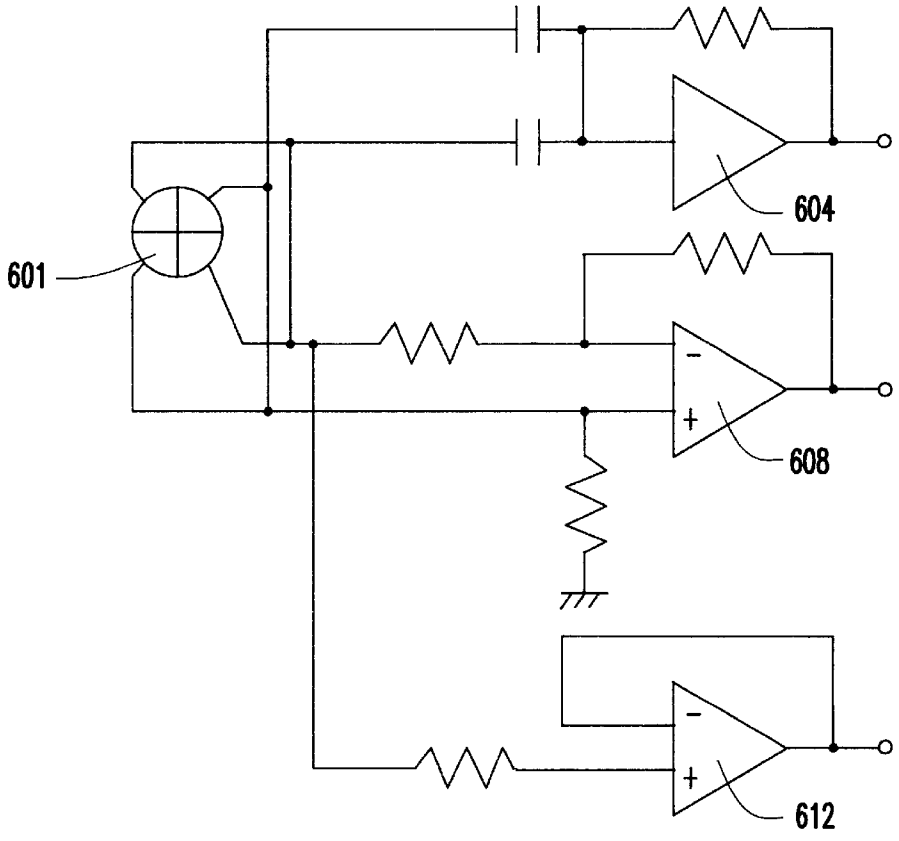

FIG.3 PRIOR ART

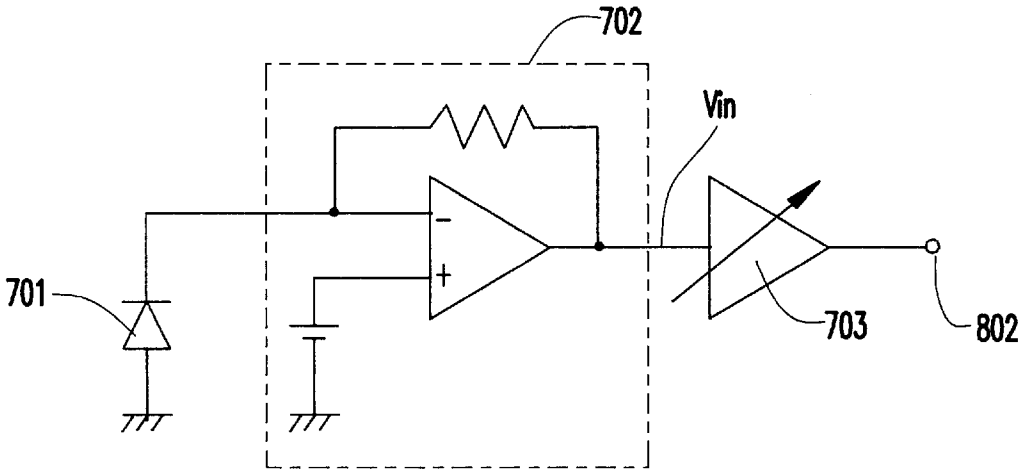

FIG.4 PRIOR ART

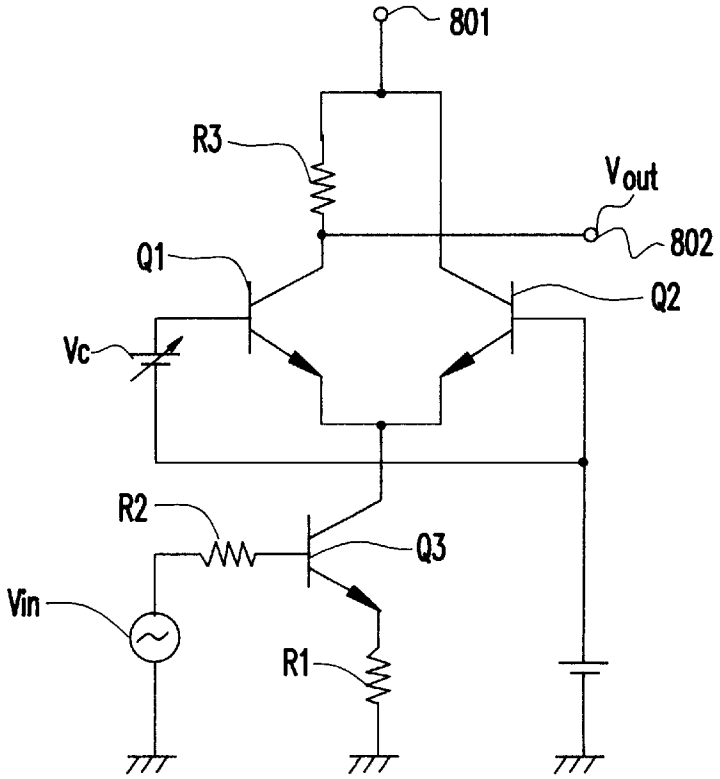

FIG.5 PRIOR ART

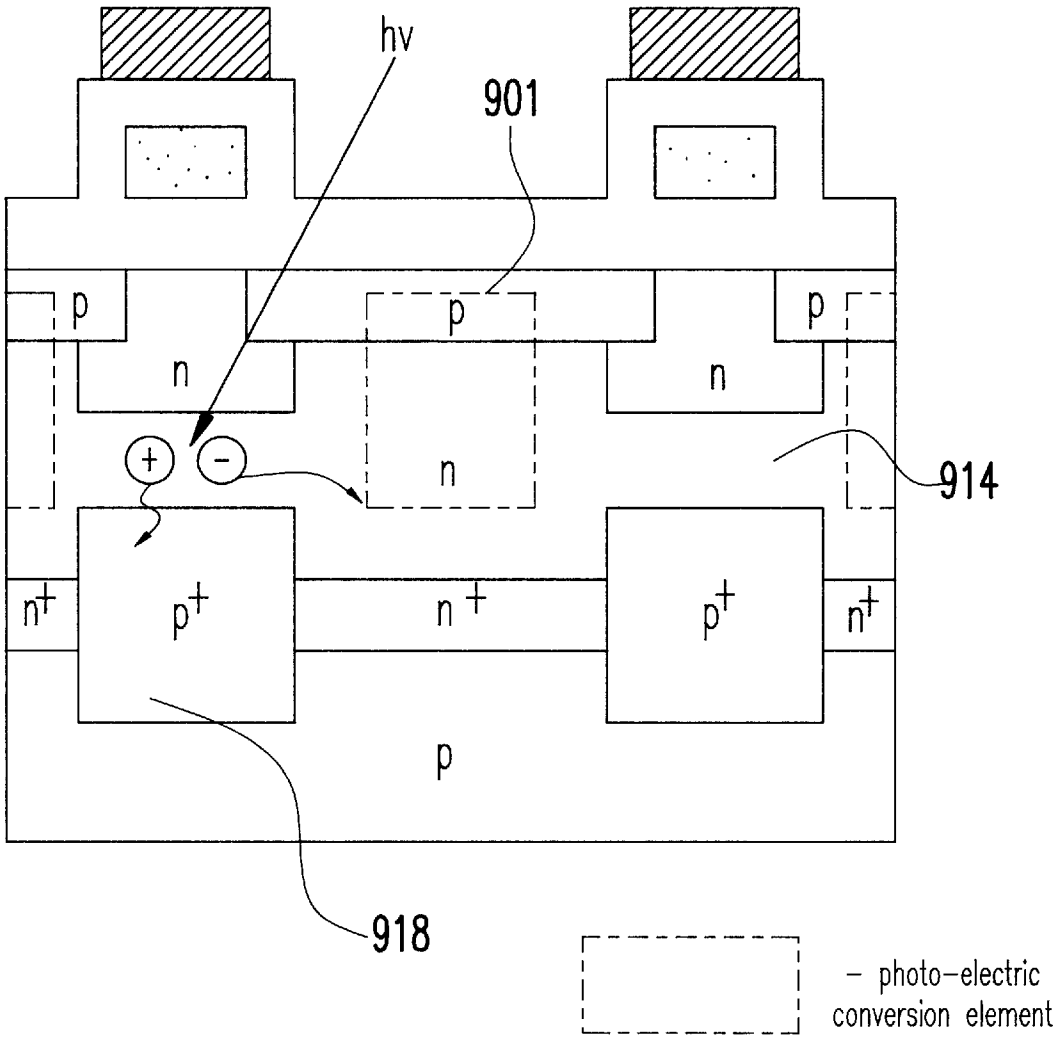

FIG.6 PRIOR ART

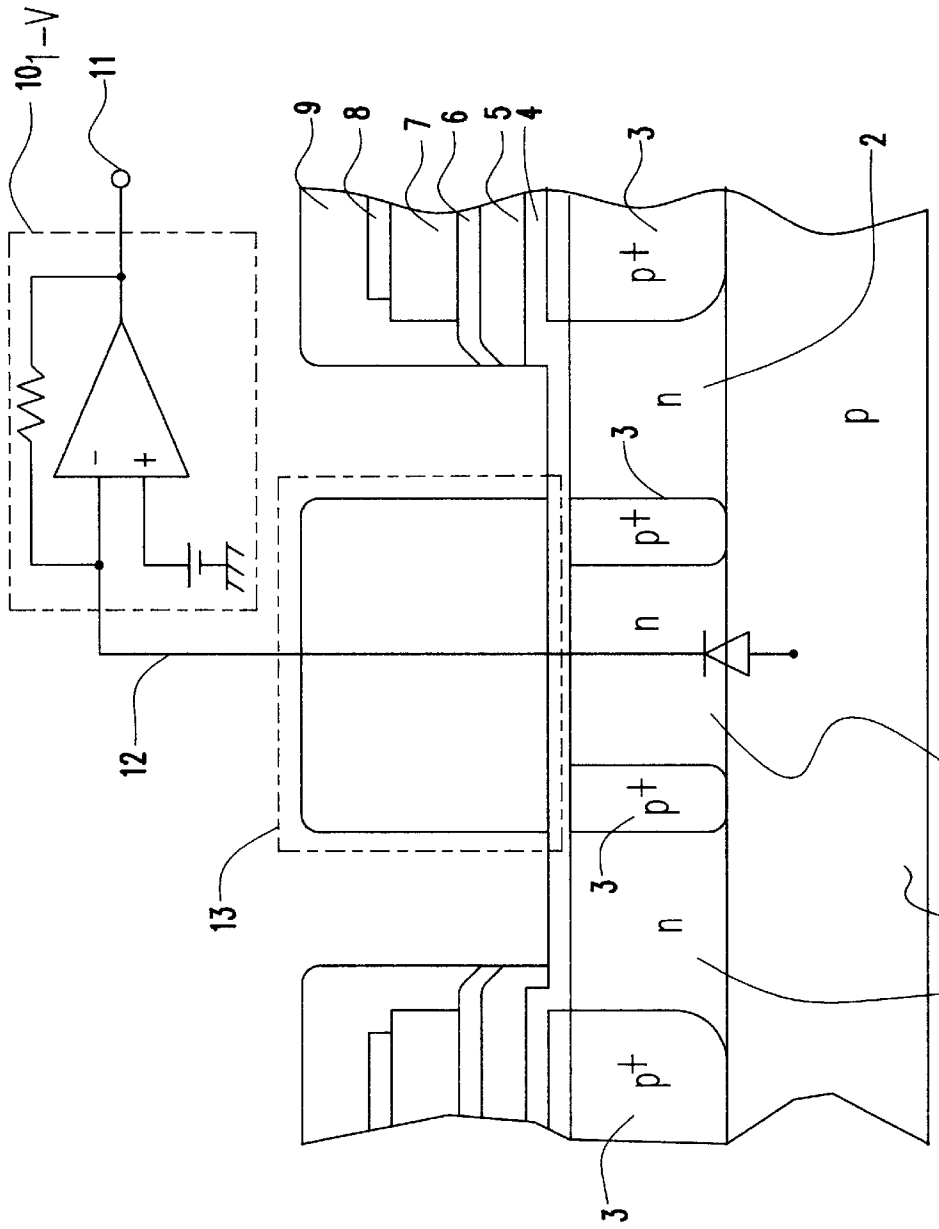

FIG.7

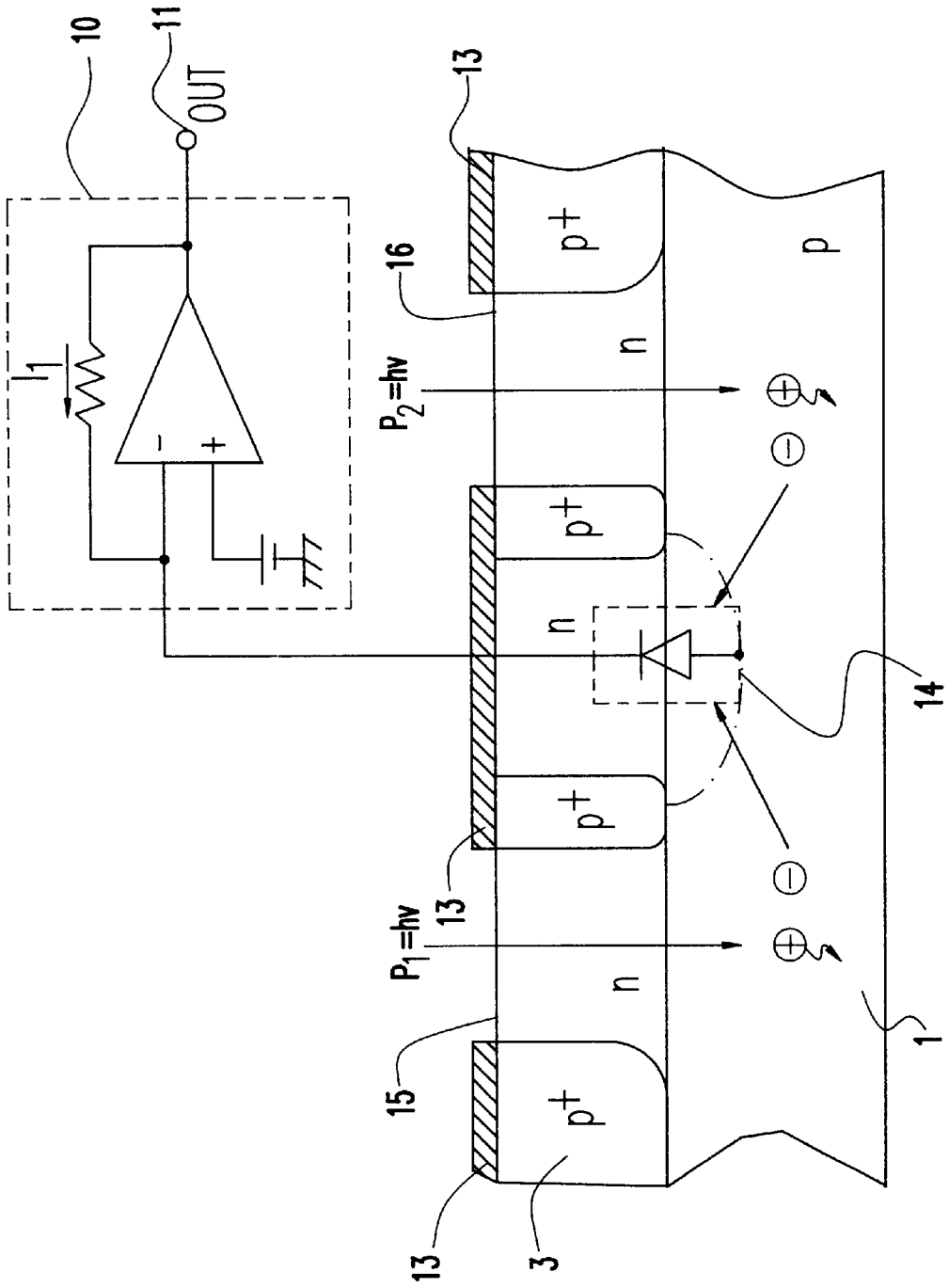

FIG.8

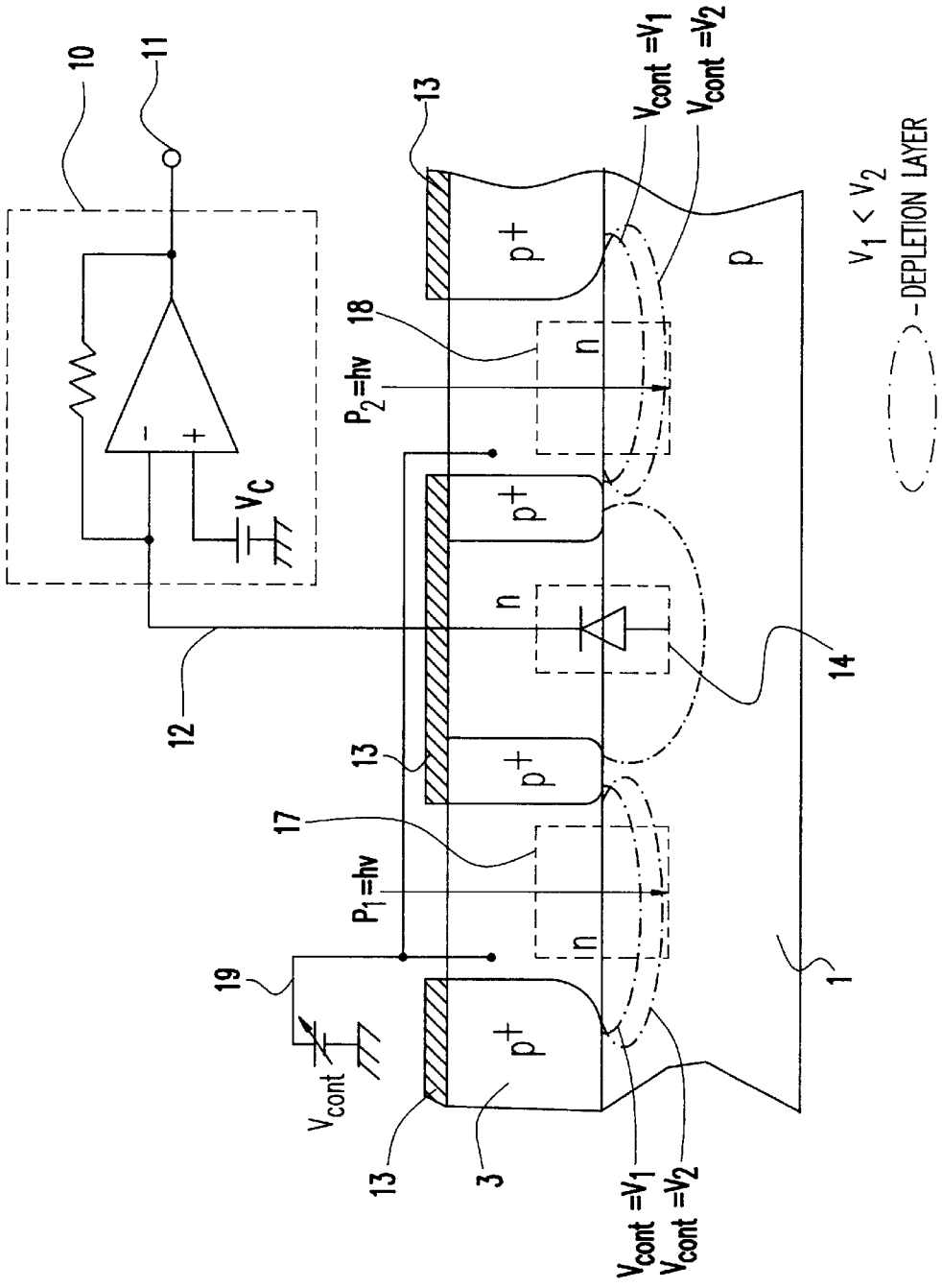
10
11
12
13
14
17
18
19
1
3
V_c
V_{cont}
P_1=hv
P_2=hv
V_{cont} =V_1
V_{cont} =V_2
p+
n
p
$V_1 < V_2$
- DEPLETION LAYER

FIG.9

PHOTODETECTOR HAVING MEANS FOR PROCESSING OPTICAL INPUT SIGNALS

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention relates to a photodetector, and more particularly to a photodetector with a signal processing capability.

2. Description of the Related Art

As shown in FIG. **1** of the accompanying drawings, one conventional adder with a photodetector comprises a pair of photodiodes **401**, **402** constructed of n-type epitaxial layers **413**, **414** and a p-type substrate **405**. and a current-to-voltage (I/V) converter **400** for converting a current signal obtained from optical signals **409**, **410** applied respectively to the photodiodes **401**, **402** into a voltage signal, the I/V converter **400** comprising an operational amplifier **403**, a feedback resistor **411**, and an output terminal **404**. The photodiodes **401**, **402** are electrically insulated from each other by a p-type high-concentration layer **407**. and connected to the I/V converter **400** by a metallic interconnection **412** for adding the optical signals.

A conventional photodetector is shown in FIG. **2** of the accompanying drawings. The photodetector shown in FIG. **2** is disclosed in Japanese laid-open patent publication No. 56274/92. The photodetector has a photodiode (photoelectric transducer) comprising a p-type well layer **502** and an n-type impurity layer **503**, and electrically separated from other elements by a p_+-type impurity layer **505**. The photodetector itself has no electric signal processing capability.

FIG. **3** of the accompanying drawings shows a signal processing circuit with a photodetector disclosed in Japanese laid-open patent publication No. 280079/86. As shown in FIG. **3**, the signal processing circuit has a four-segment photodiode **601** for producing current signals that are supplied to an FM amplifier **604**, an operational amplifier **608**, and an operational amplifier **612** which perform a signal processing operation on the supplied signals. The four-segment photodiode **601** itself has no electric signal processing capability.

A conventional applied circuit which incorporates a photodetector is illustrated in FIG. **4** of the accompanying drawings. As shown in FIG. **4**, a current signal from a photodiode **701** is converted by an I/V converter **702** into a voltage signal whose voltage gain is adjusted by an automatic gain control (AGC) circuit **703** to produce an optimum voltage signal at an output terminal **802**.

FIG. **5** of the accompanying drawings shows a specific circuit arrangement of the AGC **703** shown in FIG. **4**. As shown in FIG. **5**, the AGC circuit **703** comprises NPN transistors Q_1, Q_2, Q_3, resistors R_1, R_2, R_3, and a current supply V_{in}. Collector currents flowing into the NPN transistors Q_1, Q_2 are adjusted by controlling a control voltage applied between the bases of the NPN transistors Q_1, Q_2 for thereby controlling the gain of the AGC **703**.

If photodiodes are connected as in the four-segment photodiode **601** shown in FIG. **3**, then since crosstalk characteristics thereof are responsible for degraded signals, it is desirable to suppress such crosstalk characteristics. According to the crosstalk characteristics, a signal charge generated by light applied to a photodiode in the vicinity of an adjacent photodiode is detected as a signal of the adjacent photodiode due to diffusion and drift.

The structure of a photodiode which is designed to reduce crosstalk characteristics is illustrated in FIG. **6** of the accompanying drawings (see Japanese laid-open patent publication No. 82767/93). As shown in FIG. **6**, a p^+-type high-concentration layer **918** is disposed between photoelectric transducers **901** for absorbing dripwise holes that are generated by light applied in the vicinity of the photoelectric transducers **901**. thereby suppressing crosstalk.

However, the above conventional photodetectors with a signal processing capability have been disadvantageous in that since the photodetector (photodiodes) and the signal processor (circuit) are separate elements, the area and hence cost of the chip required are large.

SUMMARY OF THE INVENTION

It is therefore an object of the present invention to provide a photodetector with a signal processing capability which is relatively small in chip area.

To achieve the above object, there is provided in accordance with the present invention a photodetector having therein at least means for processing optical input signals.

According to the present invention, there is also provided a photodetector having therein at least means for controlling the width of a depletion layer of a pn junction to control an optical carrier.

Since a signal processing capability, which has heretofore been achieved by an external circuit, is performed in the photodetector itself, the chip area of the photodetector is reduced, and the power requirement thereof is also lowered.

The above and other objects, features, and advantages of the present invention will become apparent from the following description with references to the accompanying drawings which illustrate examples of the present invention.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. **1** is a fragmentary cross-sectional view, combined with a circuit diagram, of a conventional adder with a photodetector;

FIG. **2** is a fragmentary cross-sectional view of a conventional photodetector disclosed in Japanese laid-open patent publication No. 56274/92;

FIG. **3** is a circuit diagram of a signal processing circuit with a photodetector disclosed in Japanese laid-open patent publication No. 280079/86;

FIG. **4** is a block diagram of a conventional applied circuit which incorporates a photodetector;

FIG. **5** is a circuit diagram of a conventional AGC circuit in the circuit shown in FIG. **4**;

FIG. **6** is a cross-sectional view of a photodiode disclosed in Japanese laid-open patent publication No. 82767/93;

FIG. **7** is a fragmentary cross-sectional view, combined with a circuit diagram, of a photodetector with a signal processing capability according to a first embodiment of the present invention;

FIG. **8** is a fragmentary cross-sectional view, combined with a circuit diagram, illustrative of the manner in which the photodetector with a signal processing capability according to the first embodiment operates; and

FIG. **9** is a fragmentary cross-sectional view, combined with a circuit diagram, of a photodetector with a signal processing capability according to a second embodiment of the present invention.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

FIG. **7** shows a photodetector with a signal processing capability according to a first embodiment of the present

invention and an I/V converter coupled thereto. As shown in FIG. **7**, the photodetector includes a pn junction comprising a p-type silicon substrate **1** and an n-type epitaxial layer **2**. The pn junction provides a photodiode function or a normal diode function depending on whether a light shield **13** is present over the pn junction or not. In the absence of the light shield **13**. the pn junction serves as a photodiode. If the light shield **13** is present over the pn junction, it serves a diode. The upper surface of the pn junction is covered with a nitride film **4**. When the pn junction serves as a photodiode, only the nitride film **4** is disposed on the upper surface of the pn junction to prevent an interference which would otherwise be caused by multiple reflections of applied light.

The light shield **13** comprises a first oxide film **5**, a second oxide film **6**, an interlayer nitride film **7**. a second electrode **8**, and a covering nitride film **9**. The second electrode **8** prevents external light from reaching the pn junction.

A first electrode **12** has one end electrically connected to the n-type epitaxial layer **2** and an opposite end to an I/V converter **10**.

The pn junction is electrically insulated from other pn junctions by p-type high-concentration layers.

Operation of the photodetector with a signal processing capability according to the first embodiment will be described below with reference to FIG. **8**.

(1) Adder:

When first incident light P_1 is applied from an input area **15**. i.e., an area where there is no light shield **13** over the photodiode, electron and hole pairs are generated, and holes are absorbed by the p-type silicon substrate **1**. Due to crosstalk characteristics, electrons are attracted by a depletion layer of a diode **14** and serve as a photocurrent I_1, The photocurrent I_1 is then converted by the I/V converter **10** into a voltage signal that is applied to an output terminal **11**. The voltage signal is proportional to the incident light P_1.

When second incident light P_2 is applied from an input area **16**, a photocurrent is similarly generated and converted by the I/V converter **10** into a voltage signal that is applied to the output terminal **11**.

While the input areas **15**, **16** are optically isolated from each other, they are electrically connected to each other by the diode **14** due to the crosstalk characteristics. Therefore, the photodetector operates as a two-input adder.

(2) Ternary circuit:

The photodetector is also operable as a ternary circuit if certain limitations are imposed on incident light. Specifically, if each of the incident light P_1 and the incident light P_2 has binary levels, i.e., an H level (larger intensity) and an L level (smaller intensity), then the voltage signal at the output terminal **11** can have three levels, i.e., an H level (larger voltage level), an M level (medium voltage level), and an L level (smaller voltage level), with respect to the H, L levels of the incident light P_1 and the incident light P_2, as shown in the following Table:

TABLE

P_1	P_2	OUT
H	H	H
H	L	M
L	H	M
L	L	L

FIG. **9** shows a photodetector with a signal processing capability according to a second embodiment of the present invention. The photodetector serves as an automatic gain control (AGC) circuit. The photodetector according to the second embodiment differs from the photodetector according to the first embodiment in that a DC voltage V_{cont} is applied to photodiodes **17**, **18** to control the widths of depletion layers of the photodiodes **17**, **18**.

Operation of the photodetector is described in detail below. When the DC voltage V_{cont} is relatively low ($V_{cont}=V_1$), the widths of the depletion layers of photodiodes **17** and **18** arc smaller. Conversely, when the DC voltage V_{cont} is relatively high ($V_{cont}=V_2$), the widths of the depletion layers of photodiodes **17** and **18** are larger.

As the widths of the depletion layers of photodiodes **17** and **18** become smaller, the probability that electrons of electron and hole pairs generated by the incident light P_1 and incident light P_2 will cause crosstalk increases, The photodetector shown in FIG. **9** thus provides a gain control capabiliy since the resulting voltage signal (gain) at output terminal **11** with respect to incident light P_1 and incident light P_2 is smaller when $V_{cont}=V_1$, and greater when $V_{cont}=V_2$.

While preferred embodiments of the present invention have been described using specific terms, such description is for illustrative purposes only, and it is to be understood that changes and variations may be made without departing from the spirit or scope of the following claims.

What is claimed is:

1. A photodetector having means for processing optical input signals, said means comprising:

a p-type silicon substrate;

an n-type epitaxial layer, portions of said n-type epitaxial layer and said p-type silicon substrate forming a pn junction;

a light shield over said pn junction;

first and second light input areas disposed on respective sides of said pn junction and said light shield; and

an electrode having a first end electrically connected to the portions of said n-type epitaxial layer within said pn junction,

wherein electrons in light passing into said first and second light input areas migrate to said pn junction, said pn junction outputting to said electrode a signal corresponding to a sum of a quantity of light passing into said first light input area and a quantity of light passing into said second light input area.

2. A photodetector according to claim **1**, further comprising:

a first dopant area separating said first light input area and said pn junction and a second dopant area separating said second light input area and said pn junction.

3. A photodetector according to claim **1** further comprising:

at least means for controlling a width of a depletion layer of said pn junction.

4. A photodetector according to claim **1**,

wherein said signal is a current signal formed from a sum of a first current derived from the electrons migrating into said pn junction from said first light input area and a second current derived from the electrons migrating into said pn junction from said second light input area, and

wherein a second end of said electrode is electrically connected to a current-to-voltage converter, said converter converting said current signal into a voltage signal.

5. A photodetector according to claim **4**, wherein said current-to-voltage converter outputs three levels of voltage,

said converter outputting a first level of voltage when the light passing into said first and second input areas are of low intensity, a second level of voltage when the light passing into one of said first and second input areas is of low intensity and light passing into the other of said first and second input areas is of high intensity, and a third level of voltage when the light passing into said first and second input areas are of high intensity.

6. A photodetector according to claim **1**, wherein said first and second light input areas are formed from different portions of said n-type epitaxial layer and said p-type silicon substrate.

7. A photodetector according to claim **1**, wherein a depletion layer of said pn junction attracts the electrons in said light passing into said first and second light input areas.

8. A photodetector according to claim **1**, wherein said pn junction performs a normal diode function as a result of said light shield covering said pn junction.

9. A photodetector according to claim **1**, wherein said pn junction performs a photodiode function when said light shield is removed.

10. A photodetector comprising:

a p-type silicon substrate;

an n-type epitaxial layer over said p-type silicon substrate;

a pn junction formed from adjacent portions of said n-type epitaxial layer and said p-type silicon substrate;

a light shield over said pn junction; and

first and second photodiodes disposed on respective sides of said pn junction;

wherein electrons in light passing into said first and second photodiodes migrate to said pn junction, said pn junction outputting a signal corresponding to a sum of a quantity of light passing into said first photodiode and a quantity of light passing into said second photodiode.

11. A photodetector according to claim **10**, further comprising:

a first dopant area separating said first photodiode and said pn junction and a second dopant area separating said photodiode and said pn junction.

12. A photodetector according to claim **10**, further comprising:

a first electrode having one end connected to said pn junction;

a current-to-voltage converter connected to another end of said first electrode,

wherein said signal is a current signal formed from a sum of a first current derived from the electrons migrating into said pn junction from said first photodiode and a second current derived from the electrons migrating into said pn junction from said second photodiode, said converter converting said current signal into a voltage signal.

13. A photodetector according to claim **12**, wherein said current-to-voltage converter outputs three levels of voltage, said converter outputting a first level of voltage when the light passing into said first and second photodiodes are of low intensity, a second level of voltage when the light passing into one of said first and second photodiodes is of low intensity and light passing into the other of said first and second photodiodes is of high intensity, and a third level of voltage when the light passing into said first and second photodiodes are of high intensity.

14. A photodetector according to claim **12**, further comprising:

means for inputting DC voltage signals of different levels into said first and second photodiodes to control a gain of said photodetector.

15. A photodetector according to claim **14**, wherein said photodetector has a first gain when said means inputs a DC voltage signal of a first level into said first and second photodiodes, and wherein said photodetector has a second gain when said means inputs a DC voltage signal of a second level into said first and second photodiodes, said second gain and said second level higher than said first gain and said first level, respectively.

16. A photodetector according to claim **12**, wherein said first and second photodiodes are formed from different adjacent portions of said n-type epitaxial layer and said p-type silicon substrate.

17. A photodetector according to claim **16**, further comprising:

means for controlling widths of depletions layers of said first and second photodiodes, to thereby control a gain of said photodetector.

* * * * *